TinyLogic UHS D-Type, Flip-Flop with Preset and Clear

Description

The NC7SZ74 is a single, D–type, CMOS flip–flop with preset and clear from ON Semiconductor ultra high–speed series of TinyLogic. The device is fabricated with advanced CMOS technology to achieve ultra high speed with high output drive, while maintaining low static power dissipation over a very broad V_{CC} operating range of 1.65 V to 5.5 V V_{CC} . The inputs and outputs are high impedance when V_{CC} is 0 V. Inputs tolerate voltages up to 5.5 V, independent of V_{CC} operating voltage.

The signal level applied to the D input is transferred to the Q output during the positive–going transition of the CLK pulse.

Features

- Ultra-High Speed: tPD 2.6 ns (Typical) into 50 pF at 5 V VCC
- High Output Drive: ±24 mA at 3 V V_{CC}
- Broad V_{CC} Operating Range: 1.65 V to 5.5 V
- Power Down High–Impedance Inputs/Outputs
- Over-Voltage Tolerance Inputs Facilitate 5 V to 3 V Translation
- Proprietary Noise/EMI Reduction Circuitry

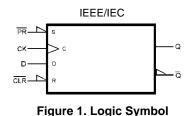


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US8	UQFN8 1.6x1.6, 0.5P
CASE 846AN	CASE 523AY

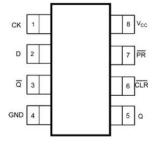
CONNECTION DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

Pin Configurations



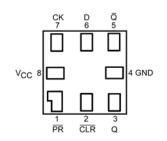
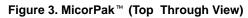


Figure 2. USB (Top View)



PIN DEFINITIONS

Pin # US8	Pin # MicroPak	Name	Description
1	7	СК	Clock Pulse Input
2	6	D	Data Input
3	5	Q	Flip–Flop Output
4	4	GND	Ground
5	3	Q	Flip–Flop Output
6	2	CLR	Direct Clear Input
7	1	PR	Direct Preset Input
8	8	Vcc	Supply Voltage

ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method [†]
NC7SZ74K8X	SZ74	8-Lead US8, JEDEC MO-187, Variation CA 3.1mm Wide	3000 Units on Tape & Reel
NC7SZ74L8X	N9	8-Lead MicroPak, 1.6 mm Wide	5000 Units on Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

FUNCTION TABLE

	Inp	uts		Output		
/CLR	/PR	D	СК	Q	/Q	Function
L	Н	Х	Х	L	Н	Clear
Н	L	Х	Х	Н	L	Preset
L	L	Х	Х	Н	н	
н	Н	L	↑	L	н	
Н	Н	Н	↑	н	L	
Н	Н	Х	\downarrow	Q _n	/Q _n	No Change

H = HIGH Logic Level

Qn = No change in data

 $X = Immaterial \qquad \qquad \downarrow = Falling Edge$

L = LOW Logic Level

Z = High Impedance

↑ = Rising Edge

ABSOLUTE MAXIMUM RATINGS

Symbol		Parameter			
Vcc	Supply Voltage		-0.5	6.5	V
Vin	DC Input Voltage		-0.5	6.5	V
Vout	DC Output Voltage		-0.5	6.5	V
Ік	DC Input Diode Current	V _{IN} < 0V		-50	mA
Іок	DC Output Diode Current	V _{OUT} < 0V		-50	mA
Ιουτ	DC Output Source/Sink Current			±50	mA
ICC or IGND	DC V _{CC} or Ground Current			±50	mA
Тѕтс	Storage Temperature Range		-65	+150	°C
TJ	Junction Temperature Under Bias	;		+150	°C
TL	Junction Lead Temperature (Sold	ering, 10 Seconds)		+260	°C
PD	Power Dissipation at +852C		250	mW	
ESD	Human Body Model, JEDEC:JES		5000	V	
	Charge Device Model: JEDEC:JE	SD22-C101		2000	1

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Conditions	Min.	Max.	Unit
Vcc	Supply Voltage Operating		1.65	5.50	V
	Supply Voltage Data Retention		1.50	5.50	
Vin	Input Voltage		0	5.5	V
Vout	Output Voltage	Active State	0	Vcc	V
		3-State	0	5.5	

RECOMMENDED OPERATING CONDITIONS (continued)

Symbol	Parameter	Conditions	Min.	Max.	Unit
t _r , t _f	Input Rise and Fall Times	V_{CC} = 1.8 V, 2.5 V ± 0.2 V	0	20	ns/V
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0	10	
		$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	5	
T _A	Operating Temperature		-40	+85	°C
0	Thermal Resistance	US8		250	°C/W
θ_{JA}		MicroPak [™] –8		280	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

NOTE: Unused inputs must be held HIGH or LOW. They may not float.

DC ELECTRICAL CHARACTERISTICS

				Τμ	<mark>م = +25</mark> ٬	°C	T _A = -40	to +85°C	
Symbol	Parameter	Vcc	Conditions	Min.	Тур.	Max.	Min.	Max.	Units
VIH	HIGH Level Control	1.65 to 1.95		0.65 V _{CC}			0.65 V _{CC}		V
	Input Voltage	2.30 to 5.50		0.70 V _{CC}			0.70 V _{CC}		
VIL	LOW Level Control	1.65 to 1.95				0.35 V _{CC}		0.35 V _{CC}	V
	Input Voltage	2.30 to 5.50				0.30 V _{CC}		0.30 V _{CC}	
Vон	HIGH Level Output Voltage	1.65	$V_{\text{IN}} = V_{\text{IH}}, \ I_{OH} = -100 \ \mu\text{A}$	1.55	1.65		1.55		V
	voltage	2.30		2.20	2.30		2.20		
		3.00		2.90	3.00		2.90		
		4.50		4.40	4.50		4.40		
		1.65	I _{OH} = -4 mA	1.29	1.52		1.29		
		2.30	I _{OH} = -8 mA	1.90	2.15		1.90		
		3.00	I _{OH} = -16 mA	2.40	2.80		2.40		
		3.00	I _{OH} = -24 mA	2.30	2.68		2.30		
		4.50	I _{OH} = -32 mA	3.80	4.20		3.80		
Vol	LOW Level Control Output Voltage	1.65	$V_{IN} = V_{IH}, I_{OL} = 100 \ \mu A$			0.10		0.10	V
	Oulput voltage	2.30				0.10		0.10	
		3.00				0.10		0.10	
		4.50				0.10		0.10	
		1.65	I _{OL} = 4 mA		0.10	0.24		0.24	
		2.30	I _{OL} = 8 mA		0.10	0.30		0.30	
		3.00	I _{OL} = 16 mA		0.15	0.40		0.40	
		3.00	I _{OL} = 24 mA		0.22	0.55		0.55	
		4.50	I _{OL} = 32 mA		0.22	0.55		0.55	
lin	Input Leakage Current	1.65 to 5.5	$0 \le V_{IN} \le 5.5 V$			±0.1		±1.0	μA
IOFF	Power Off Leakage Current	0	V _{IN} or V _{OUT} = 5.5 V			1		10	μΑ
lcc	Quiescent Supply Current	1.65 to 5.50	V _{IN} = 5.5 V, GND			1		10	μΑ

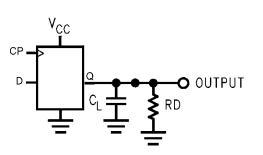
AC ELECTRICAL CHARACTERISTICS

				Т	A = +25°	C	$T_A = -40$	to +85°C																	
Symbol	Parameter	V _{cc}	Conditions	Min.	Тур.	Max.	Min.	Max.	Units	Figure															
fмах	Maximum Clock Frequency	1.80 ± 0.15	$C_L = 15 \text{ pF}$	75			75		ns	Figure 4															
	riequency	2.50 ± 0.20	$R_D = 1 M\Omega$ $S_1 = Open$	150			150			Figure 8															
		3.30 ± 0.30		200			200																		
		5.00 ± 0.50		250			250																		
		3.30 ± 0.50	$C_L = 50 \text{ pF}$	175			175																		
		5.00 ± 0.50	R _D = 500 Ω, S ₁ = Open	200			200																		
tplh, tphl	Propagation Delay CK	1.80 ± 0.15	C _L = 15pF,		6.5	12.5		13.0	ns	Figure 4															
	to Q, /Q	2.50 ± 0.20	- R _D = 1 MΩ S ₁ = Open		3.8	7.5		8.0		Figure 6															
		3.30 ± 0.30			2.8	6.5		7.0																	
		5.00 ± 0.50			2.2	4.5		5.0																	
		3.30 ± 0.30	C _L = 50 pF		3.4	7.0		7.5																	
		5.00 ± 0.50	$R_D = 500 \Omega,$ S ₁ = Open		2.6	5.0		5.5																	
tplh, tphl	Propagation Delay	1.80 ± 0.15	C ₁ = 15 pF,		6.5	14.0		14.5	ns	Figure 4															
	/CLR, /PR to Q, /Q	2.50 ± 0.20	$R_{L}^{-} = 1 M\Omega$ S ₁ = Open		3.8	9.0		9.5	-	Figure 6															
		3.30 ± 0.30			2.8	6.5		7.0																	
		5.00 ± 0.50			2.2	5.0		5.5																	
		3.30 ± 0.30	C _L = 50 pF,		3.4	7.0		7.5																	
		5.00 ± 0.50	$R_D = 500 \Omega$, $S_1 = Open$		2.6	5.0		5.5																	
t _S	Setup Time CK to D	1.80 ± 0.15	C _L = 15 pF,	6.5			6.5		ns	ns	ns	ns	ns	ns	ns	ns	ns	ns	ns	ns	ns	ns	ns	ns	Figure 4
		2.50 ± 0.20	$R_{L} = 1 M\Omega$ S ₁ = Open	3.5			3.5		-	Figure 7															
		3.30 ± 0.30		2.0			2.0		-																
		5.00 ± 0.50		1.5			1.5		-																
		3.30 ± 0.30	C _L = 50 pF,	2.0			2.0																		
		5.00 ± 0.50	$R_D = 500 \Omega$, $S_1 = Open$	1.5			1.5																		
t _H	Hold Time, CK to D	1.80 ± 0.15	C ₁ = 15 pF,	0.5			0.5		ns	Figure 4															
		2.50 ± 0.20	$R_{L}^{-} = 1 M\Omega$ S ₁ = Open	0.5			0.5		-	Figure 7															
		3.30 ± 0.30		0.5			0.5		-																
		5.00 ± 0.50		0.5			0.5		-																
		3.30 ± 0.30	C _L = 50 pF,	0.5			0.5																		
		5.00 ± 0.50	$R_D = 500 \Omega$, $S_1 = Open$	0.5			0.5																		
t _W	Pulse Width, CK,	1.80 ± 0.15	C ₁ = 15 pF,	6.0			6.0		ns	Figure 4															
	/PR, /CLR	2.50 ± 0.20	$R_{L} = 1 M\Omega$ S ₁ = Open	4.0		1	4.0		1	Figure 8															
		3.30 ± 0.30		3.0		1	3.0		1																
		5.00 ± 0.50	1	2.0		1	2.0		1																
		3.30 ± 0.30	C _L =50pF,	3.0		1	3.0		1																
			$R_{D} = 500\Omega$,	2.0	1	1	2.0		1																

				Т	A = +25°	C	$T_A = -40$	to +85°C		
Symbol	Parameter	V _{CC}	Conditions	Min.	Тур.	Max.	Min.	Max.	Units	Figure
t REC	Recover Time /CLR,	1.80 ± 0.15	C _L = 15 pF, R _I = 1 MΩ	8.0			8.0		ns	Figure 7
	/PR to CK	2.50 ± 0.20	$S_1 = Open$	4.5			4.5			
		3.30 ± 0.30		3.0			3.0			
		5.00 ± 0.50		3.0			3.0			
		3.30 ± 0.30	$C_{L} = 50 \text{ pF},$	3.0			3.0			
		5.00 ± 0.50	R _D = 500 Ω, S ₁ = Open	3.0			3.0			
CIN	Input Capacitance	0			3				pF	
Соит	Output Capacitance	0			4				pF	
CPD	Power Dissipation	3.30			10				pF	
	Capacitance (Note 1)	5.00			12				1	

AC ELECTRICAL CHARACTERISTICS (continued)

C_{PD} is defined as the value of the internal equivalent capacitance which is derived from dynamic operating current consumption (I_{CCD}) at 1. no output loading and operating at 50% duty cycle. C_{PD} is related to I_{CCD} dynamic operating current by the expression: $I_{CCD} = (C_{PD})(V_{CC})(f_{IN}) + (I_{CC}static).$



2. CL includes load and stray capacitance. Input PRR = 1.0 MHz $t_w = 500$ ns.



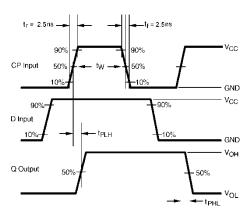


Figure 6. AC Waveforms

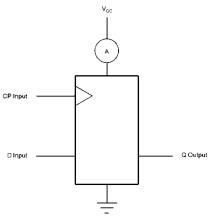


Figure 5. AC Test Circuit

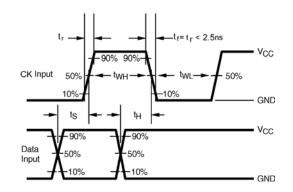


Figure 7. AC Waveforms

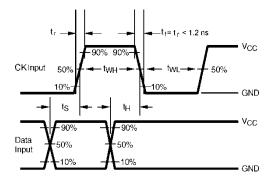
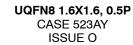


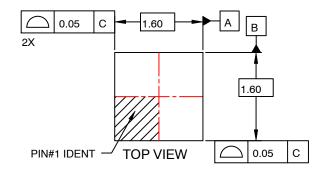
Figure 8. AC Waveforms

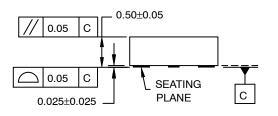
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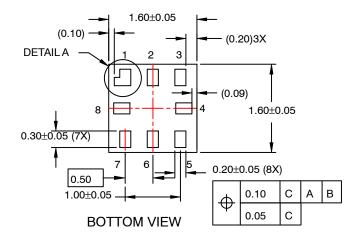


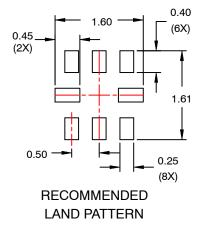
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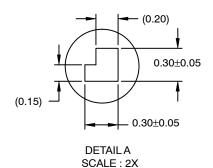
SIDE VIEW





NOTES:

- A. PACKAGE CONFORMS TO JEDEC MO-255 VARIATION UAAD.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
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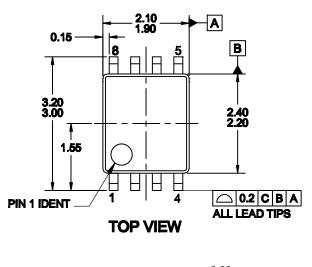
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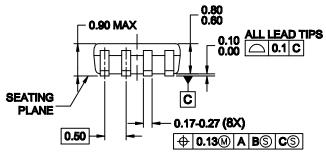
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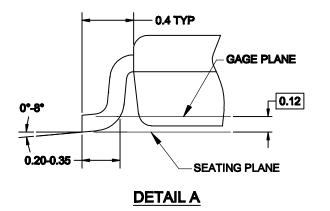
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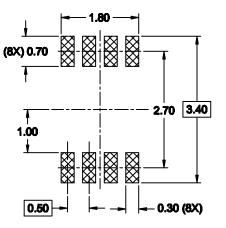
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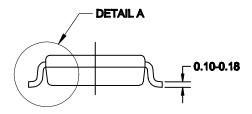




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